

## Silicon PNP Power Transistors

2SA1643

## DESCRIPTION

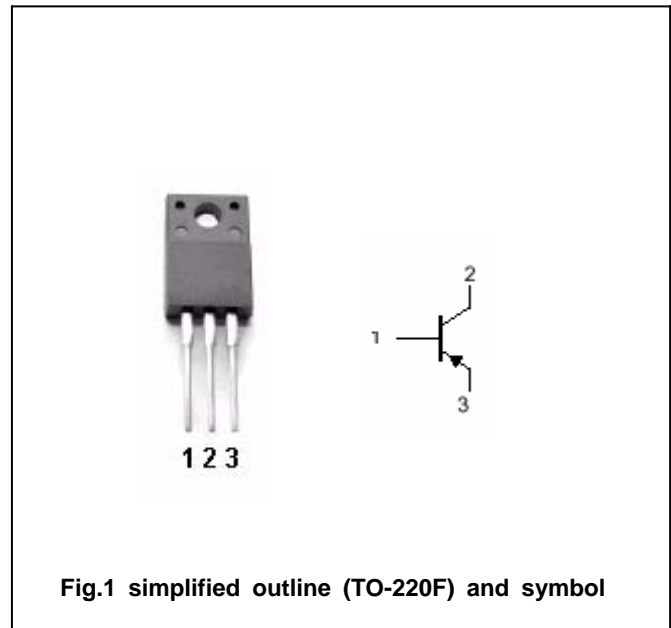
- With TO-220F package
- Complement to type 2SC4327
- Low collector saturation voltage

## APPLICATIONS

- For power switching applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



## Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-50	V
$V_{CEO}$	Collector-emitter voltage	Open base	-35	V
$V_{EBO}$	Emitter-base voltage	Open collector	-7	V
$I_C$	Collector current		-7	A
$P_C$	Collector dissipation	$T_C=25^\circ\text{C}$	25	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA ; I <sub>B</sub> =0	-80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-1mA ; I <sub>C</sub> =0	-7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-5A ; I <sub>B</sub> =-0.3A			-0.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-50V ; I <sub>E</sub> =0			-10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-7V ; I <sub>C</sub> =0			-10	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-5A ; V <sub>CE</sub> =-2V	50			
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =1A ; V <sub>CE</sub> =-12V		75		MHz

